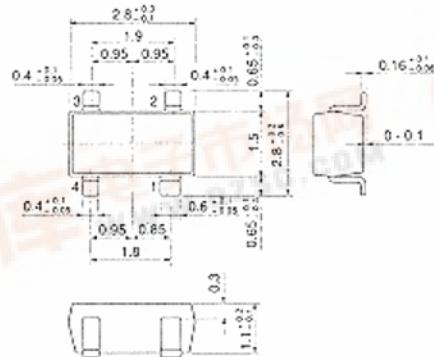


# 3SK191

GaAs DUAL GATE FET

UHF TV TUNER RF AMPLIFIER

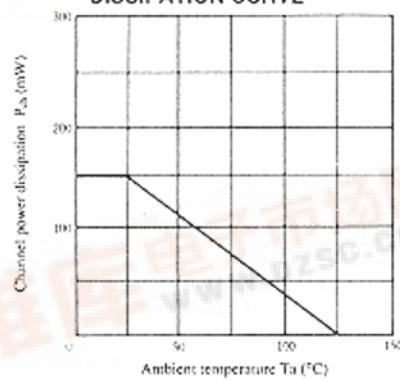


(MPAK-4)

1. Source
  2. Gate 1
  3. Gate 2
  4. Drain
- (Dimensions in mm)

**■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

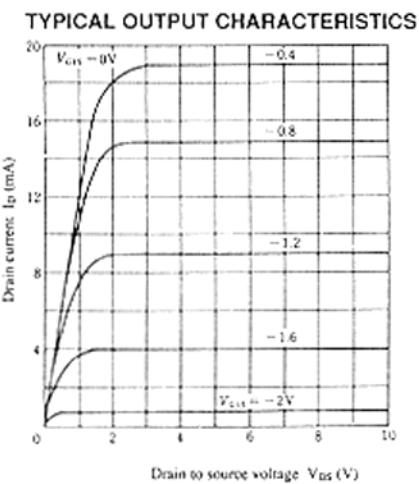
Item	Symbol	3SK191	Unit
Drain to source voltage	V <sub>DS</sub>	12	V
Gate 1 to source voltage	V <sub>G1S</sub>	+0.5, -6	V
Gate 2 to source voltage	V <sub>G2S</sub>	+0.5, -6	V
Drain current	I <sub>D</sub>	80	mA
Channel power dissipation	P <sub>ch</sub>	150	mW
Channel temperature	T <sub>ch</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

**MAXIMUM CHANNEL POWER DISSIPATION CURVE****■ ELECTRICAL CHARACTERISTICS (Ta=25°C)**

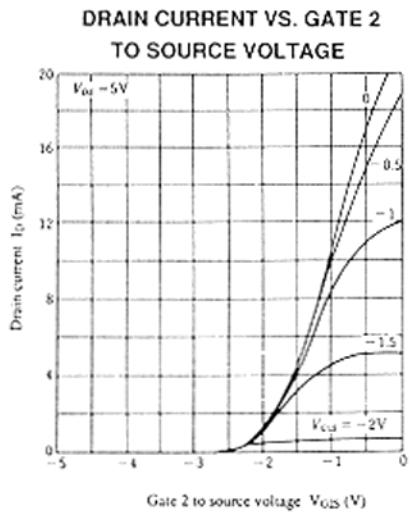
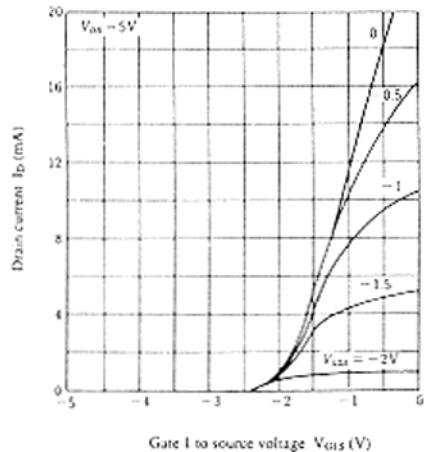
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain to source breakdown voltage	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 50μA, V <sub>G1S</sub> = -6V, V <sub>G2S</sub> = 0	12	—	—	V
Gate 1 to source breakdown voltage	V <sub>(BR)G1SS</sub>	I <sub>G1</sub> = -10μA, V <sub>G2S</sub> = V <sub>DS</sub> = 0	-6	—	—	V
Gate 2 to source breakdown voltage	V <sub>(BR)G2SS</sub>	I <sub>G2</sub> = -10μA, V <sub>G1S</sub> = V <sub>DS</sub> = 0	-6	—	—	V
Gate 1 cutoff current	I <sub>G1SS</sub>	V <sub>G1S</sub> = -5V, V <sub>G2S</sub> = V <sub>DS</sub> = 0	—	—	-5	μA
Gate 2 cutoff current	I <sub>G2SS</sub>	V <sub>G1S</sub> = -5V, V <sub>G1S</sub> = V <sub>DS</sub> = 0	—	—	-5	μA
Drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 5V, V <sub>G1S</sub> = V <sub>G2S</sub> = 0	10	—	32	mA
Gate 1 to source cutoff voltage	V <sub>G1S(off)</sub>	V <sub>DS</sub> = 5V, V <sub>G2S</sub> = 0, I <sub>D</sub> = 100μA	—	—	-5	V
Gate 2 to source cutoff voltage	V <sub>G2S(off)</sub>	V <sub>DS</sub> = 5V, V <sub>G1S</sub> = 0, I <sub>D</sub> = 100μA	—	—	-4	V
Forward transfer admittance	I <sub>yKL</sub>	V <sub>DS</sub> = 5V, V <sub>G2S</sub> = 0, I <sub>D</sub> = 10mA, f = 1kHz	10	—	—	mS
Input capacitance	C <sub>iss</sub>		—	0.55	1.0	pF
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 5V, V <sub>G1S</sub> = V <sub>G2S</sub> = -6V f = 1MHz	—	0.3	0.6	pF
Reverse transfer capacitance	C <sub>rss</sub>		—	0.02	0.05	pF
Power gain	PG	V <sub>DS</sub> = 5V, V <sub>G2S</sub> = 0, I <sub>D</sub> = 10mA	12	16.6	—	dB
Noise figure	NF	f = 900MHz	—	1.5	3.0	dB

Marking is "NT-".

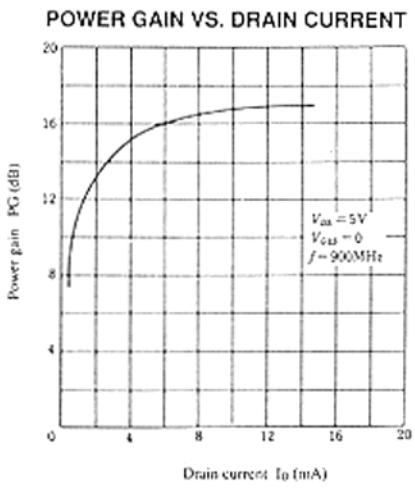
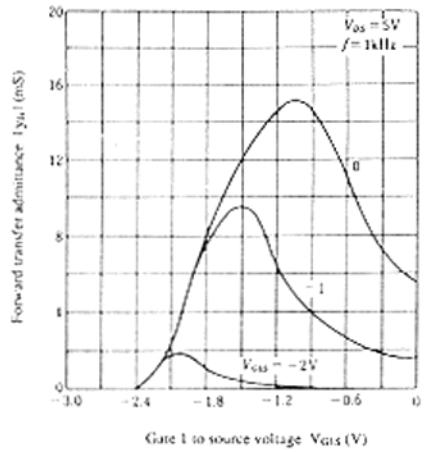
## 3SK191



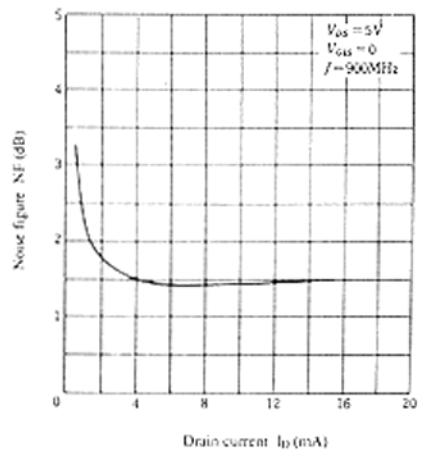
DRAIN CURRENT VS. GATE 1  
TO SOURCE VOLTAGE

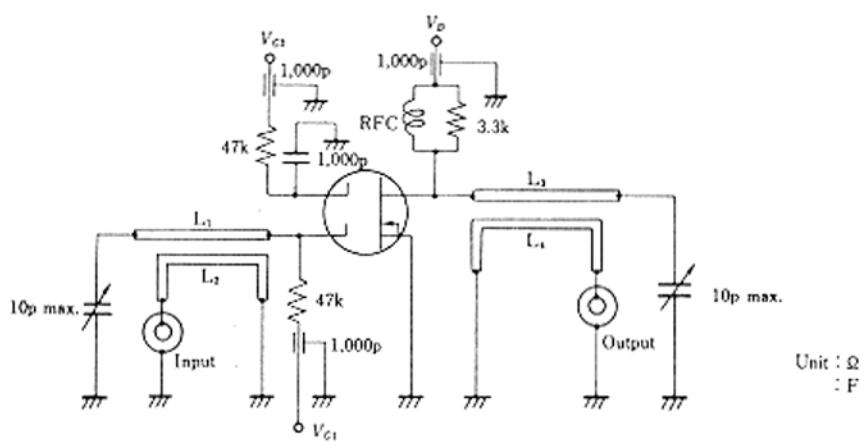


FORWARD TRANSFER ADMITTANCE VS.  
GATE 1 TO SOURCE VOLTAGE



NOISE FIGURE VS. DRAIN CURRENT



**■ PG, NF TEST CIRCUIT**

RFC : ø1mm Enamelled Copper Wire, Inside dia 6mm, 3 Pattern